

Reg. No.

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B.E / B.TECH. DEGREE EXAMINATION, MAY 2023

Third Semester

EE18301 – ELECTRON DEVICES AND CIRCUITS*Electrical and Electronics Engineering***(Regulation 2018A)****TIME: 3 HOURS****MAX. MARKS: 100**

- CO 1** Describe and analyse different types of PN devices.
CO 2 Describe and analyse different types of current and Voltage controlled devices
CO 3 Analyse performance of devices using small signal model
CO 4 Design and implementation of various electronic devices in circuits

PART- A (10 x 2 = 20 Marks)

(Answer all Questions)

	CO	RBT LEVEL
1. Define dynamic resistance.	1	1
2. A half-wave rectifier has its peak value (V_m) as 10V. Calculate the average and RMS values of current.	1	3
3. What are the consequences of early effect in transistor?	2	2
4. Consider the single stage CE amplifier with $R_s=1K\Omega$ and $R_L=1.2K\Omega$. Calculate the current gain if $h_{fe}=50$ and $h_{oc}=25\mu A/V$.	3	3
5. Compare BJT and FET.	2	3
6. Draw the small signal model of common source amplifier.	3	2
7. Why neutralization used in tuned amplifiers?	4	3
8. A voltage series feedback amplifier has a voltage gain with feedback as 83.33 and feedback ratio as 0.01. Calculate the voltage gain of the amplifier without feedback.	4	3
9. List the applications of opto-coupler.	1	2
10. Why silicon is not a preferable LED material?	1	2

PART- B (5 x 14 = 70 Marks)

	Marks	CO	RBT LEVEL
11. (a) (i) Explain the Volt ampere characteristics of pn junction diode in forward and reverse bias.	(7)	1	3
(ii) Draw the circuit diagram of half wave rectifier for producing a positive output voltage .Explain the circuit operation and sketch the waveforms.	(7)	1	3

(OR)

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|---------|---|------|---|---|
| (b) | (i) Briefly discuss about the capacitance effect of pn junction under reverse bias condition. | (7) | 1 | 3 |
| | (ii) Explain the operation of Zener diode as voltage regulator. | (7) | 1 | 3 |
| 12. (a) | Explain the operation of NPN transistor in CE configuration with its input and output characteristics. Also define active, saturation and cutoff regions. | (14) | 2 | 3 |
| | (OR) | | | |
| (b) | Explain the need for biasing and different biasing methods of BJT. | (14) | 2 | 3 |
| 13. (a) | Analyze the performance of common drain MOSFET amplifier and derive its input impedance, output impedance and voltage gain. | (14) | 3 | 4 |
| | (OR) | | | |
| (b) | For a CS amplifier, draw the small signal equivalent circuit and determine the expression for voltage gain, input impedance and output impedance. | (14) | 3 | 4 |
| 14. (a) | Analyze the operation of differential amplifier for common mode and differential mode inputs and derive its CMRR. | (14) | 4 | 4 |
| | (OR) | | | |
| (b) | Draw the circuit for voltage series feedback and derive the expression for input impedance, output impedance and voltage gain. | (14) | 4 | 4 |
| 15. (a) | Discuss the principle and operation of a Colpitts oscillator with a circuit. Also deduce an expression for frequency of oscillations. | (14) | 4 | 3 |
| | (OR) | | | |
| (b) | With neat diagram explain the Wien bridge oscillator and derive an expression for frequency of oscillations. | (14) | 4 | 3 |

PART- C (1 x 10 = 10 Marks)

(Q.No.16 is compulsory)

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LEVEL |
|---|-------|----|--------------|
| 16. The device parameters for an n-Channel JFET are: Maximum current $I_{DSS} = 10\text{mA}$, Pinch off voltage, $V_P = -4\text{V}$. Calculate the drain current for (a) $V_{GS} = 0$, (b) $V_{GS} = -1.0\text{V}$ and (c) $V_{GS} = -4\text{V}$. | (10) | 2 | 4 |